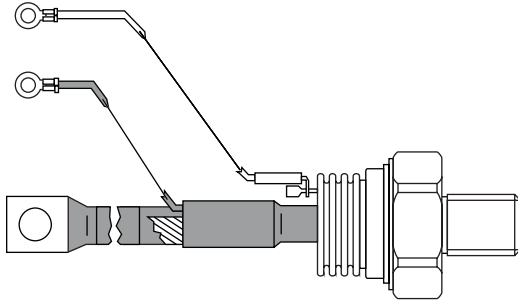


## Inverter Grade Thyristors (Stud Version), 300 A



TO-209AE (TO-118)

**FEATURES**

- Center amplifying gate
- High surge current capability
- Low thermal impedance
- High speed performance
- Compression bonding
- Lead (Pb)-free
- Designed and qualified for industrial level


**RoHS  
COMPLIANT**
**PRODUCT SUMMARY**

|             |       |
|-------------|-------|
| $I_{T(AV)}$ | 300 A |
|-------------|-------|

**TYPICAL APPLICATIONS**

- Inverters
- Choppers
- Induction heating
- All types of force-commutated converters

**MAJOR RATINGS AND CHARACTERISTICS**

| PARAMETER         | TEST CONDITIONS | VALUES      | UNITS             |
|-------------------|-----------------|-------------|-------------------|
| $I_{T(AV)}$       |                 | 300         | A                 |
|                   | $T_C$           | 65          | °C                |
| $I_{T(RMS)}$      |                 | 471         | A                 |
| $I_{TSM}$         | 50 Hz           | 7950        |                   |
|                   | 60 Hz           | 8320        |                   |
| $I^2t$            | 50 Hz           | 316         | kA <sup>2</sup> s |
|                   | 60 Hz           | 288         |                   |
| $V_{DRM}/V_{RRM}$ |                 | 400 to 1200 | V                 |
| $t_q$             |                 | 10/20       | μs                |
| $T_J$             |                 | - 40 to 125 | °C                |

**ELECTRICAL SPECIFICATIONS**
**VOLTAGE RATINGS**

| TYPE NUMBER | VOLTAGE CODE | $V_{DRM}/V_{RRM}$ , MAXIMUM REPETITIVE PEAK VOLTAGE<br>V | $V_{RSM}$ , MAXIMUM NON-REPETITIVE PEAK VOLTAGE<br>V | $I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM<br>mA |
|-------------|--------------|--|--|--|
| ST303S      | 04           | 400  | 500  | 50   |
|             | 08           | 800  | 900  |  |
|             | 12           | 1200   | 1300   |  |

# ST303SPbF Series



Vishay High Power Products Inverter Grade Thyristors  
(Stud Version), 300 A

| CURRENT CARRYING CAPABILITY      |           |     |           |     |           |      |       |
|----------------------------------|-----------|-----|-----------|-----|-----------|------|-------|
| FREQUENCY                        |           |     |           |     |           |      | UNITS |
| 50 Hz                            | 670       | 470 | 1050      | 940 | 5240      | 4300 | A     |
| 400 Hz                           | 480       | 330 | 1021      | 710 | 1800      | 1270 |       |
| 1000 Hz                          | 230       | 140 | 760       | 470 | 730       | 430  |       |
| 2500 Hz                          | 35        | -   | 150       | -   | 90        | -    |       |
| Recovery voltage $V_R$           | 50        |     | 50        |     | 50        |      | V     |
| Voltage before turn-on $V_D$     | $V_{DRM}$ |     | $V_{DRM}$ |     | $V_{DRM}$ |      |       |
| Rise of on-state current $di/dt$ | 50        |     | -         |     | -         |      | A/μs  |
| Case temperature                 | 40        | 65  | 40        | 65  | 40        | 65   | °C    |
| Equivalent values for RC circuit | 10/0.47   |     | 10/0.47   |     | 10/0.47   |      | Ω/μF  |

| ON-STATE CONDUCTION  |               |   |                            |   |        |                    |
|--|---------------|---|----------------------------|---|--------|--------------------|
| PARAMETER  | SYMBOL        | TEST CONDITIONS   |                            |   | VALUES | UNITS              |
| Maximum average on-state current at case temperature       | $I_{T(AV)}$   | 180° conduction, half sine wave   |                            |   | 300    | A                  |
|  |               |   |                            |   | 65     | °C                 |
| Maximum RMS on-state current                               | $I_{T(RMS)}$  | DC at 45 °C case temperature  |                            |   | 471    | A                  |
| Maximum peak, one half cycle, non-repetitive surge current | $I_{TSM}$     | t = 10 ms   | No voltage reappplied      | Sinusoidal half wave, initial $T_J = T_J$ maximum | 7950   |                    |
|  |               | t = 8.3 ms  |                            |   | 8320   |                    |
|  |               | t = 10 ms   | 100 % $V_{RRM}$ reappplied |   | 6690   |                    |
|  |               | t = 8.3 ms  |                            |   | 7000   |                    |
| Maximum $I^2t$ for fusing                                  | $I^2t$        | t = 10 ms   | No voltage reappplied      |   | 316    | kA <sup>2</sup> s  |
|  |               | t = 8.3 ms  |                            |   | 288    |                    |
|  |               | t = 10 ms   | 100 % $V_{RRM}$ reappplied |   | 224    |                    |
|  |               | t = 8.3 ms  |                            |   | 204    |                    |
| Maximum $I^2\sqrt{t}$ for fusing                           | $I^2\sqrt{t}$ | t = 0.1 to 10 ms, no voltage reappplied   |                            |   | 3160   | kA <sup>2</sup> √s |
| Maximum peak on-state voltage                              | $V_{TM}$      | $I_{TM} = 1255$ A, $T_J = T_J$ maximum, $t_p = 10$ ms sine wave pulse                   |                            |   | 2.16   | V                  |
| Low level value of threshold voltage                       | $V_{T(TO)1}$  | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum |                            |   | 1.44   |                    |
| High level value of threshold voltage                      | $V_{T(TO)2}$  | $(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum                                      |                            |   | 1.46   |                    |
| Low level value of forward slope resistance                | $r_{f1}$      | $(16.7\% \times \pi \times I_{T(AV)} < I < \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum |                            |   | 0.57   | mΩ                 |
| High level value of forward slope resistance               | $r_{f2}$      | $(I > \pi \times I_{T(AV)})$ , $T_J = T_J$ maximum                                      |                            |   | 0.56   |                    |
| Maximum holding current                                    | $I_H$         | $T_J = 25$ °C, $I_T > 30$ A   |                            |   | 600    | mA                 |
| Typical latching current                                   | $I_L$         | $T_J = 25$ °C, $V_A = 12$ V, $R_a = 6$ Ω, $I_G = 1$ A                                   |                            |   | 1000   |                    |



| <b>SWITCHING</b>   |         |  |        |            |
|--|---------|--|--------|------------|
| PARAMETER  | SYMBOL  | TEST CONDITIONS  | VALUES | UNITS      |
| Maximum non-repetitive rate of rise of turned-on current | di/dt   | $T_J = T_J$ maximum, $V_{DRM} = \text{Rated } V_{DRM}$<br>$I_{TM} = 2 \times di/dt$  | 1000   | A/ $\mu$ s |
| Typical delay time                                       | $t_d$   | $T_J = 25^\circ\text{C}$ , $V_{DM} = \text{Rated } V_{DRM}$ , $I_{TM} = 50$ A DC, $t_p = 1 \mu\text{s}$<br>Resistive load, gate pulse: 10 V, 5 $\Omega$ source | 0.80   | $\mu$ s    |
| Maximum turn-off time                                    | minimum | $T_J = T_J$ maximum,<br>$I_{TM} = 550$ A, commutating di/dt = 40 A/ $\mu$ s<br>$V_R = 50$ V, $t_p = 500 \mu\text{s}$ , dV/dt = 200 V/ $\mu$ s                  | 10     |            |
|  | maximum |  | 20     |            |

| <b>BLOCKING</b>                                    |                        |  |        |            |
|--|------------------------|--|--------|------------|
| PARAMETER  | SYMBOL                 | TEST CONDITIONS  | VALUES | UNITS      |
| Maximum critical rate of rise of off-state voltage | dV/dt                  | $T_J = T_J$ maximum, linear to 80 % $V_{DRM}$ ,<br>higher value available on request | 500    | V/ $\mu$ s |
| Maximum peak reverse and off-state leakage current | $I_{RRM}$<br>$I_{DRM}$ | $T_J = T_J$ maximum, rated $V_{DRM}/V_{RRM}$ applied                                 | 50     | mA         |

| <b>TRIGGERING</b>                           |             |   |        |       |
|---|-------------|---|--------|-------|
| PARAMETER                                   | SYMBOL      | TEST CONDITIONS   | VALUES | UNITS |
| Maximum peak gate power                     | $P_{GM}$    | $T_J = T_J$ maximum, f = 50 Hz, d% = 50                   | 60     | W     |
| Maximum average gate power                  | $P_{G(AV)}$ |   | 10     |       |
| Maximum peak positive gate current          | $I_{GM}$    | $T_J = T_J$ maximum, $t_p \leq 5$ ms                      | 10     | A     |
| Maximum peak positive gate voltage          | + $V_{GM}$  |   | 20     |       |
| Maximum peak negative gate voltage          | - $V_{GM}$  |   | 5      |       |
| Maximum DC gate current required to trigger | $I_{GT}$    | $T_J = 25^\circ\text{C}$ , $V_A = 12$ V, $R_a = 6 \Omega$ | 200    | mA    |
| Maximum DC gate voltage required to trigger | $V_{GT}$    |   | 3      | V     |
| Maximum DC gate current not to trigger      | $I_{GD}$    | $T_J = T_J$ maximum, rated $V_{DRM}$ applied              | 20     | mA    |
| Maximum DC gate voltage not to trigger      | $V_{GD}$    |   | 0.25   | V     |

| <b>THERMAL AND MECHANICAL SPECIFICATIONS</b> |            |   |                   |                     |
|--|------------|---|-------------------|---------------------|
| PARAMETER                                    | SYMBOL     | TEST CONDITIONS                               | VALUES            | UNITS               |
| Maximum operating junction temperature range | $T_J$      |   | - 40 to 125       | $^\circ\text{C}$    |
| Maximum storage temperature range            | $T_{Stg}$  |   | - 40 to 150       |                     |
| Maximum thermal resistance, junction to case | $R_{thJC}$ | DC operation                                  | 0.10              | K/W                 |
| Maximum thermal resistance, case to heatsink | $R_{thCS}$ | Mounting surface, smooth, flat and greased    | 0.03              |                     |
| Mounting force, $\pm 10$ %                   |            | Non-lubricated threads                        | 48.5<br>(425)     | N · m<br>(lbf · in) |
| Approximate weight                           |            |   | 535               | g                   |
| Case style                                   |            | See dimensions - link at the end of datasheet | TO-209AE (TO-118) |                     |

# ST303SPbF Series



Vishay High Power Products Inverter Grade Thyristors  
(Stud Version), 300 A

| $\Delta R_{thJ-hs}$ CONDUCTION |                       |                        |   |       |
|--------------------------------|-----------------------|------------------------|---|-------|
| CONDUCTION ANGLE               | SINUSOIDAL CONDUCTION | RECTANGULAR CONDUCTION | TEST CONDITIONS                         | UNITS |
| 180°                           | 0.011                 | 0.008                  | T <sub>J</sub> = T <sub>J</sub> maximum | K/W   |
| 120°                           | 0.013                 | 0.014                  |   |       |
| 90°                            | 0.017                 | 0.018                  |   |       |
| 60°                            | 0.025                 | 0.026                  |   |       |
| 30°                            | 0.041                 | 0.042                  |   |       |

**Note**

- The table above shows the increment of thermal resistance R<sub>thJ-hs</sub> when devices operate at different conduction angles than DC

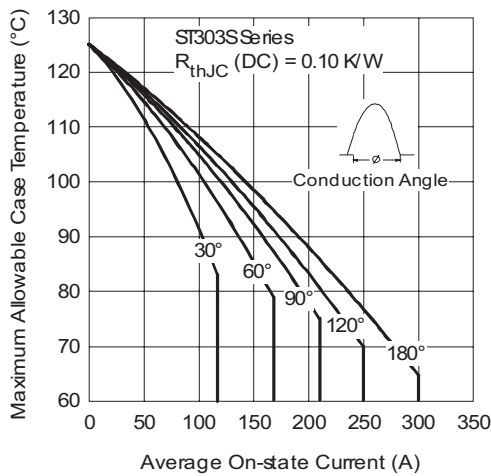


Fig. 1 - Current Ratings Characteristics

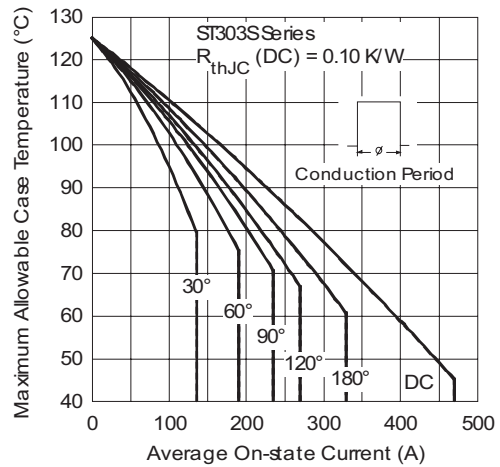


Fig. 2 - Current Ratings Characteristics

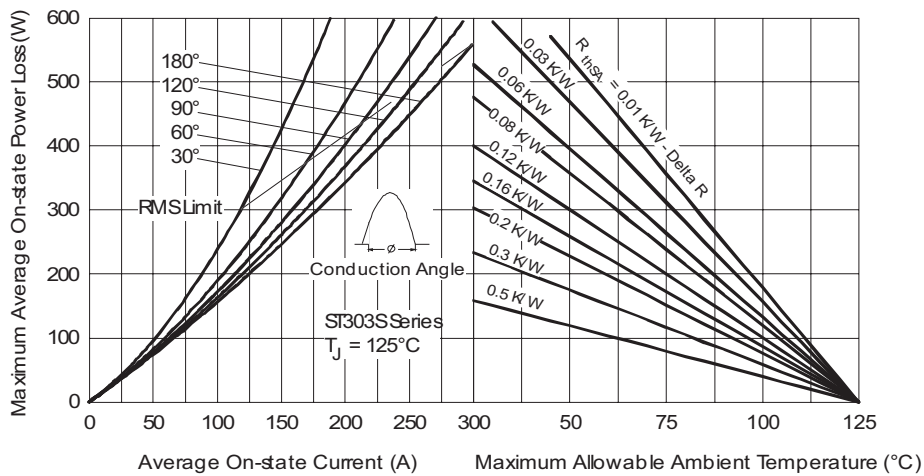


Fig. 3 - On-State Power Loss Characteristics

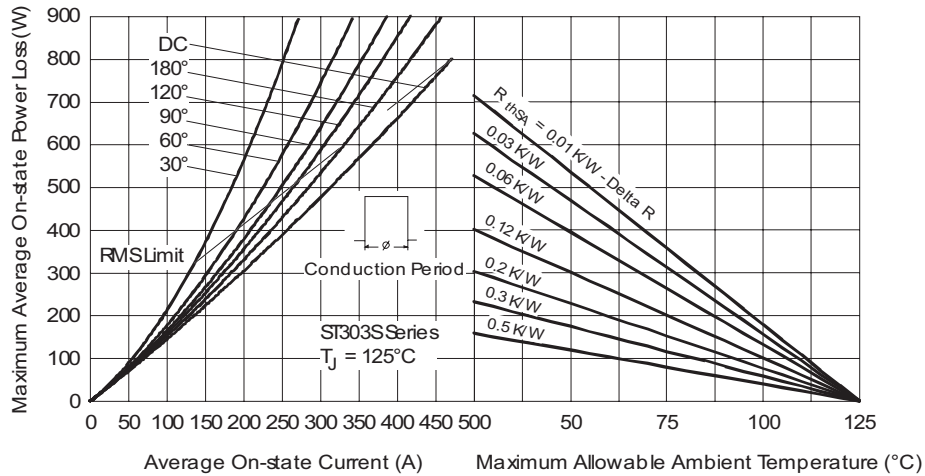


Fig. 4 - On-State Power Loss Characteristics

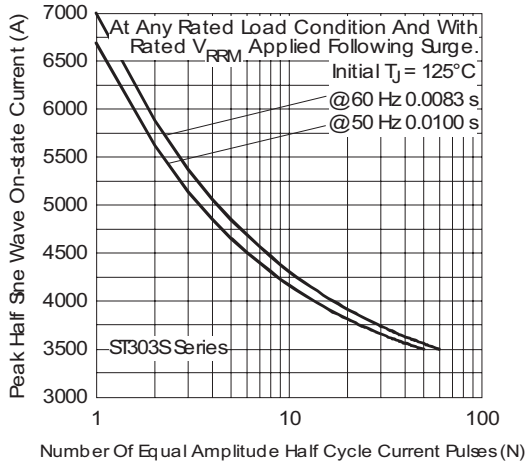


Fig. 5 - Maximum Non-Repetitive Surge Current

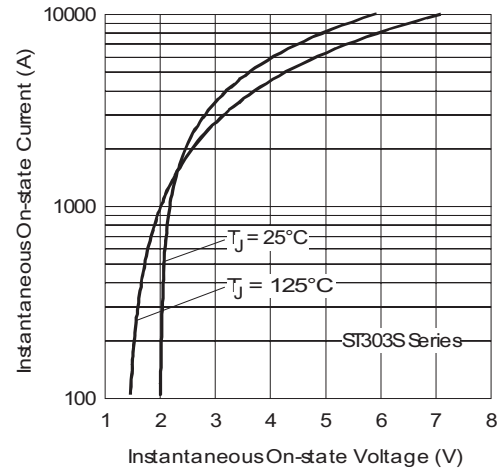


Fig. 7 - On-State Voltage Drop Characteristics

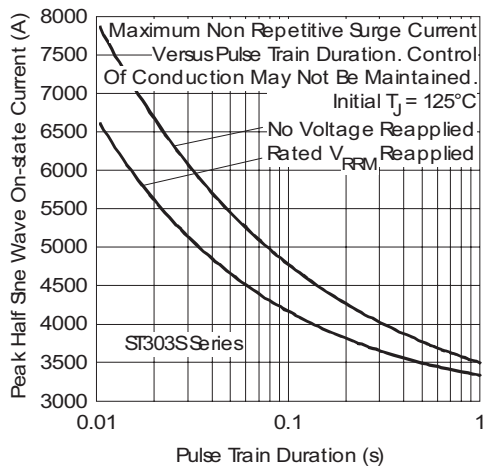


Fig. 6 - Maximum Non-Repetitive Surge Current

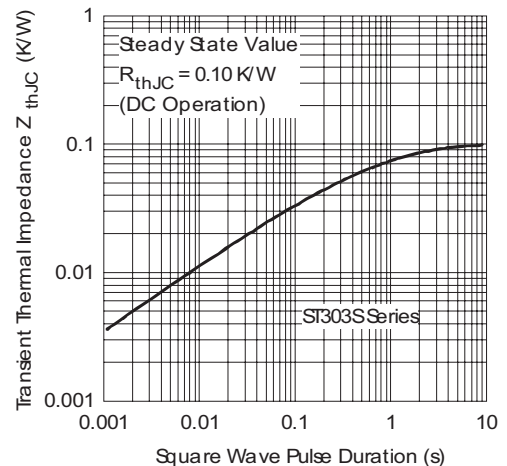


Fig. 8 - Thermal Impedance  $Z_{thJC}$  Characteristics

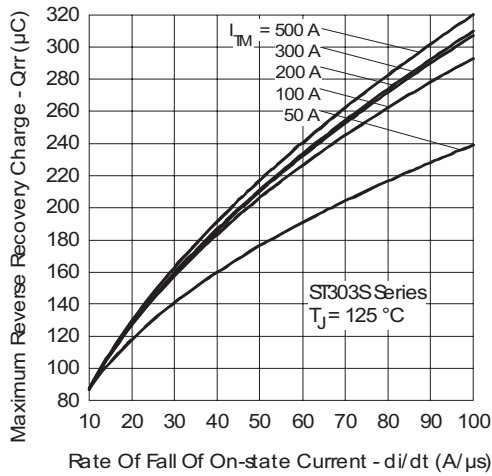


Fig. 9 - Reverse Recovered Charge Characteristics

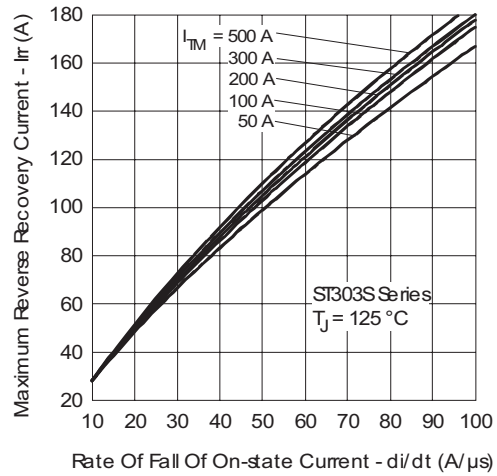


Fig. 10 - Reverse Recovery Current Characteristics

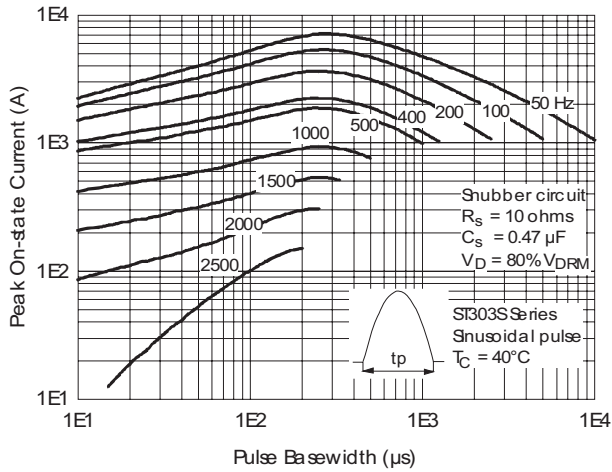


Fig. 11 - Frequency Characteristics

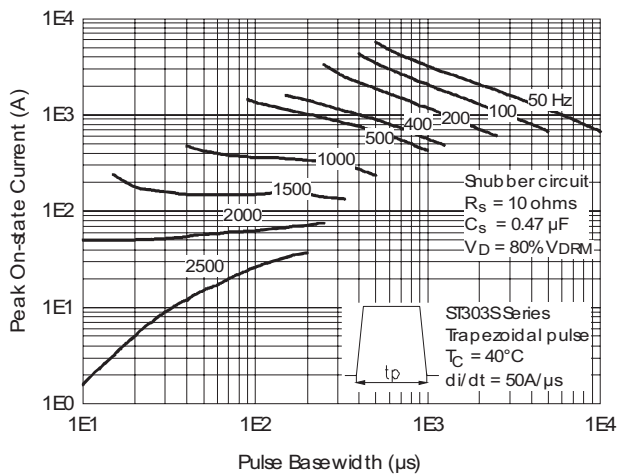
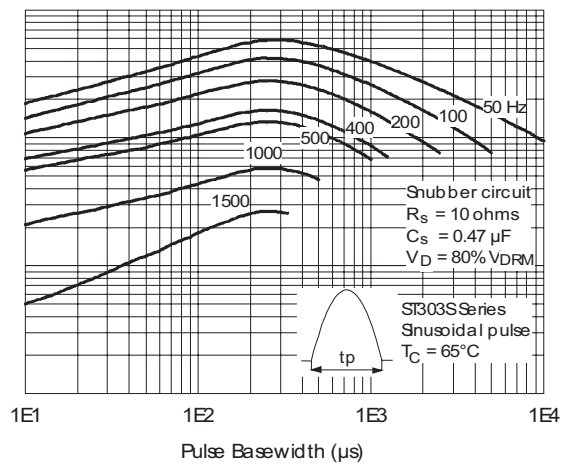
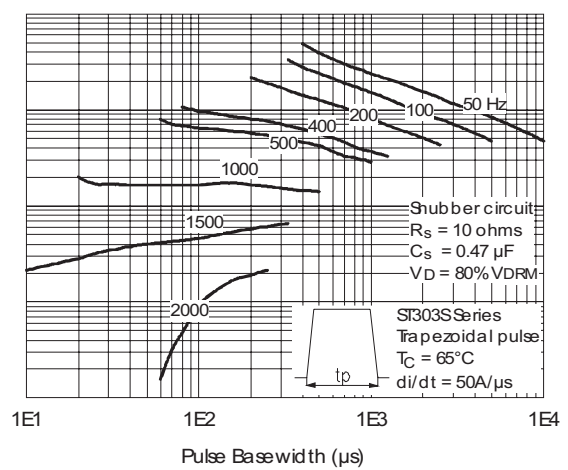


Fig. 12 - Frequency Characteristics



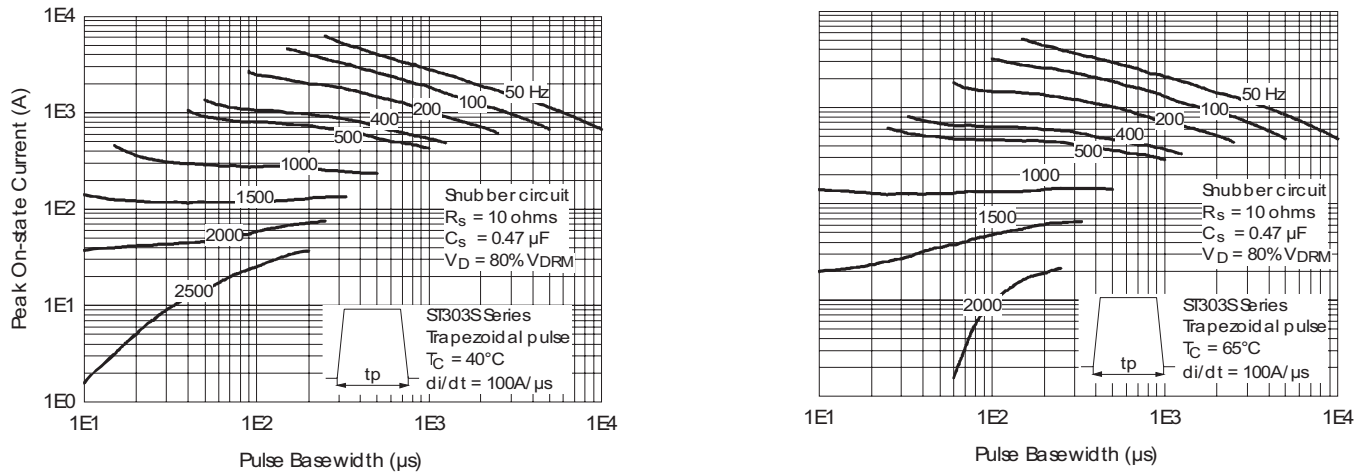


Fig. 13 - Frequency Characteristics

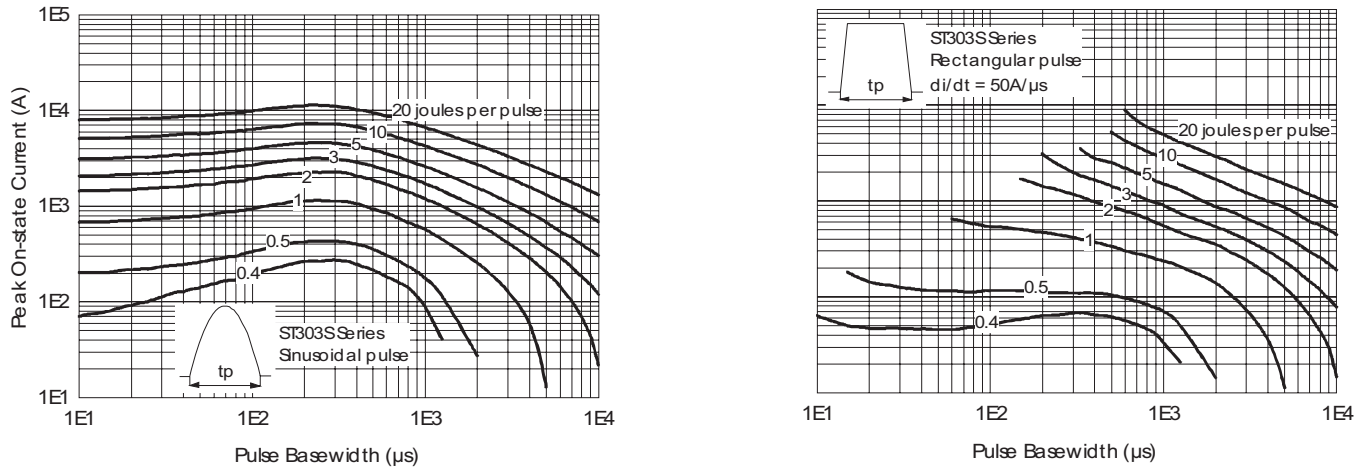


Fig. 14 - Maximum On-State Energy Power Loss Characteristics

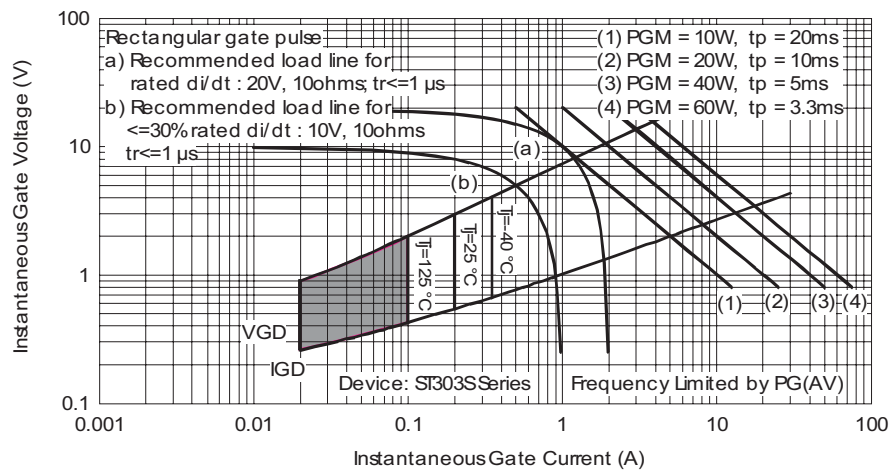


Fig. 15 - Gate Characteristics

# ST303SPbF Series



Vishay High Power Products Inverter Grade Thyristors  
(Stud Version), 300 A

## ORDERING INFORMATION TABLE

|             |    |    |   |   |    |   |   |   |   |   |
|-------------|----|----|---|---|----|---|---|---|---|---|
| Device code | ST | 30 | 3 | S | 12 | P | F | K | 0 | P |
|             | ①  | ②  | ③ | ④ | ⑤  | ⑥ | ⑦ | ⑧ | ⑨ | ⑩ |

- 1** - Thyristor
- 2** - Essential part number
- 3** - 3 = Fast turn-off
- 4** - S = Compression bonding stud
- 5** - Voltage code x 100 =  $V_{RRM}$   
(see Voltage Ratings table)
- 6** - P = Stud base 3/4" 16UNF-2A
- 7** - Reapplied dV/dt code (for  $t_q$  test condition)
- 8** -  $t_q$  code
- 9** - 0 = Eyelet terminals  
(gate and auxiliary cathode leads)  
1 = Fast-on terminals  
(gate and auxiliary cathode leads)
- 10** - Lead (Pb)-free

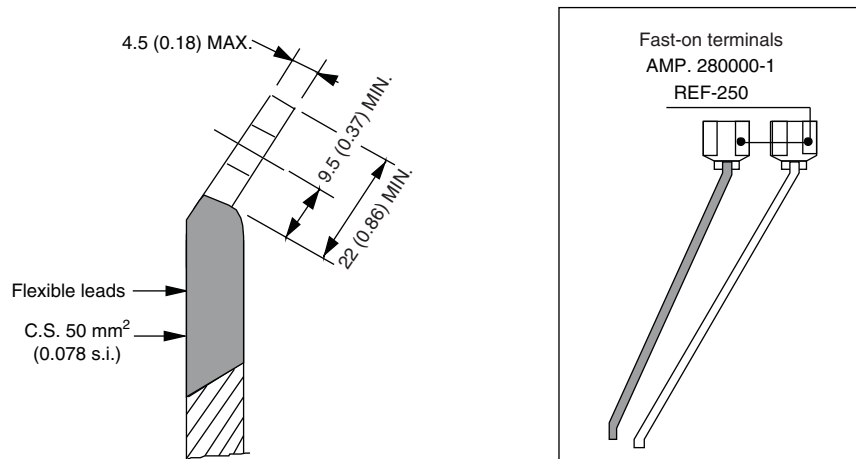
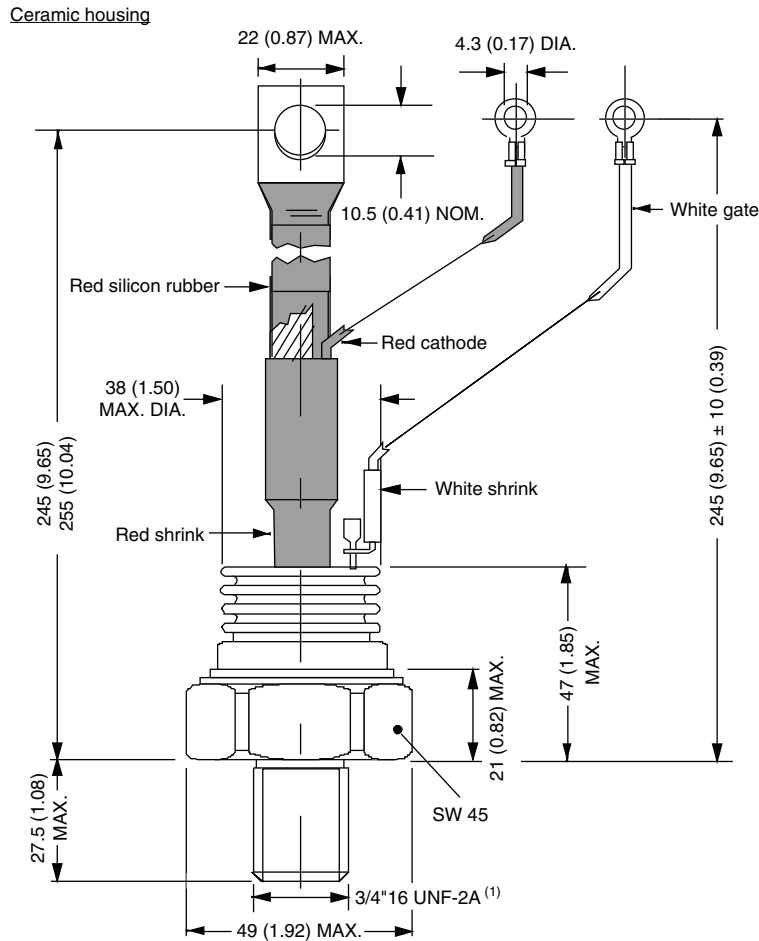
| dV/dt - $t_q$ combinations available        |                    |     |
|---|--------------------|-----|
|   | dV/dt (V/ $\mu$ s) | 200 |
| $t_q$ ( $\mu$ s)<br>up to 800 V             | 10                 | FN  |
|   | 20                 | FK  |
| $t_q$ ( $\mu$ s)<br>only for<br>1000/1200 V | 20                 | FK  |

| LINKS TO RELATED DOCUMENTS |   |
|----------------------------|---|
| Dimensions                 | <a href="http://www.vishay.com/doc?95080">http://www.vishay.com/doc?95080</a> |



## TO-209AE (TO-118)

**DIMENSIONS** in millimeters (inches)



**Note**

<sup>(1)</sup> For metric device: M24 x 1.5 - length 21 (0.83) maximum



## Disclaimer

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**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

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- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
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- Наличие сертификата ISO.

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- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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